风光欣技术资料

C1027

—NPN silicon —

■■**APPLICATION:** High Voltage Applications.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	120	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	800	mA
Collector Power Dissipation	P_C	1	W
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

TO-92L

1. Emitter 2. Collector 3. Base

■■**ELECTRICAL CHARACTERISTICS（Ta=25℃）**

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	80		240		V_{CE}= 5V，I_C= 100mA
Collector Cut-off Current	I_{CBO}			0.1	μA	V_{CB}= 120V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.1	μA	V_{EB}= 5V，I_C=0
Collectoe-Base Breakdown Voltage	BV_{CBO}	120			V	I_C= 1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	120			V	I_C= 10mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E= 1mA，I_C=0
Base-Emitter Voltage	V_{BE}			1	V	V_{CE}= 5V，I_C= 500mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			1	V	I_C= 500mA，I_B= 50mA
Gain bandwidth product	f_T	50	120		MHz	I_C= 100mA，V_{CE}= 5V
Common Base Output Capacitance	C_{ob}			30	pF	V_{CB}= 10V, I_E=0, f = 1MHz

■■hFE **Classification And Marking**

Classification	O	Y
h_{FE}	80～160	120～240